120V NPN SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT23

Feature

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Feature

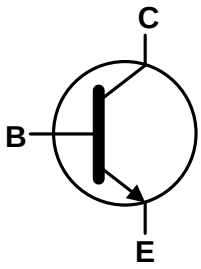
- BV_{CEO} > 120V
- I_C = 1A Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- 500mW Power Dissipation
- h_{FE} characterised up to 1A for high current gain hold up
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

Mechanical Data

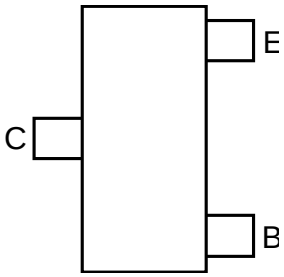
- Case: SOT23 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

SOT23 (Type DN)

Top View



Device Symbol



Top View
Pin-Out

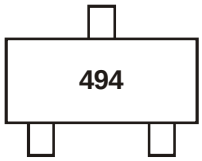
Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FMMT494QTA	Automotive	494	7	8	3,000
FMMT494QTC	Automotive	494	13	8	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT23 (Type DN)



494 = Product Type Marking Code

© Diodes Incorporated

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Base Current	I_B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{\theta JL}$	197	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

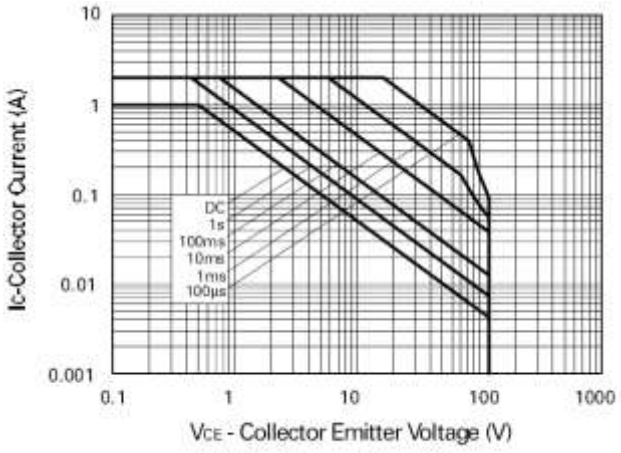
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

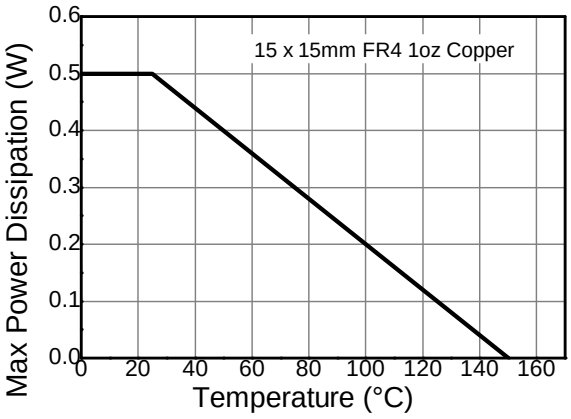
Notes:
6. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

© Diodes Incorporated

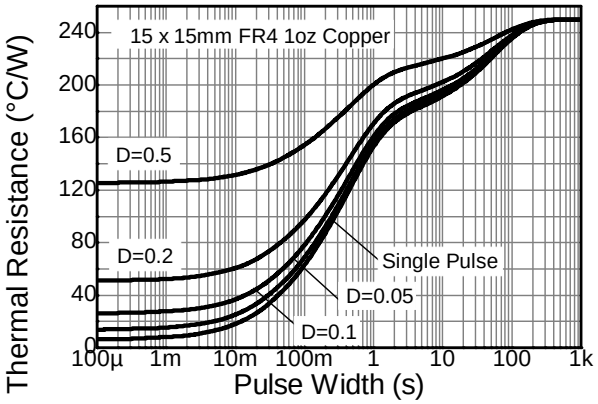
Thermal Characteristics and Derating Information



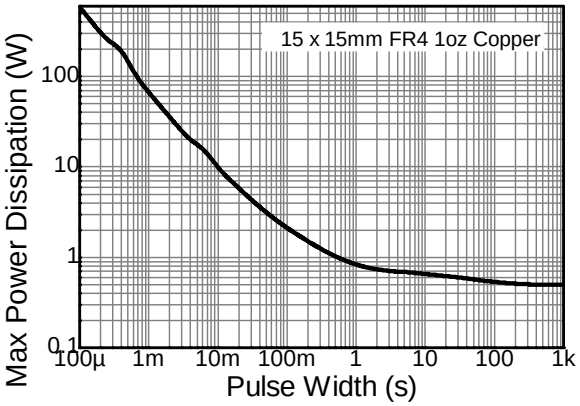
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

© Diodes Incorporated

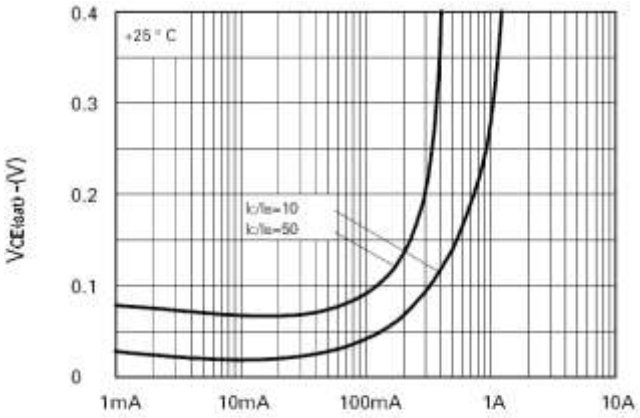
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	140	—	—	V	I_C = 100µA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	120	—	—	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	I_E = 100µA
Collector Cutoff Current	I_{CBO}	—	—	100	nA	V_{CB} = 120V
Emitter Cutoff Current	I_{EBO}	—	—	100	nA	V_{EB} = 5V
Collector Emitter Cutoff Current	I_{CES}	—	—	100	nA	V_{CE} = 120V
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	100	—	—	—	I_C = 1mA, V_{CE} = 10V
		100	—	300		I_C = 250mA, V_{CE} = 10V
		60	—	—		I_C = 500mA, V_{CE} = 10V
		20	—	—		I_C = 1A, V_{CE} = 10V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	—	200	mV	I_C = 250mA, I_B = 25mA
		—	—	300		I_C = 500mA, I_B = 50mA
Base-Emitter Turn-On Voltage(Note 9)	$V_{BE(on)}$	—	—	1.0	V	I_C = 500mA, V_{CE} = 10V
Base-Emitter Saturation Voltage(Note 9)	$V_{BE(sat)}$	—	—	1.1	V	I_C = 500mA, I_B = 50mA
Output Capacitance	C_{obo}	—	—	10	pF	V_{CB} = 10V, f = 1MHz
Transition Frequency	f_T	100	—	—	MHz	V_{CE} = 50V, I_C = 10mA, f = 100MHz

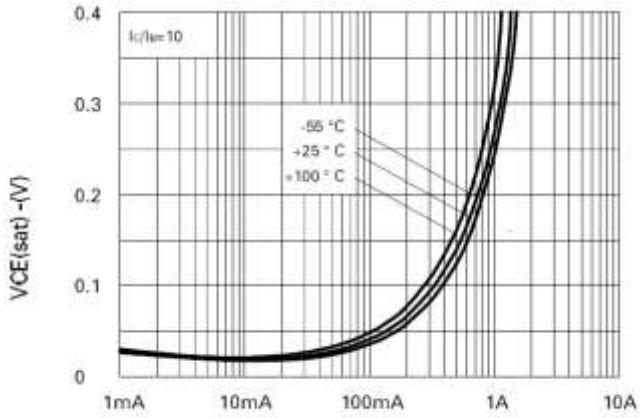
Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

© Diodes Incorporated

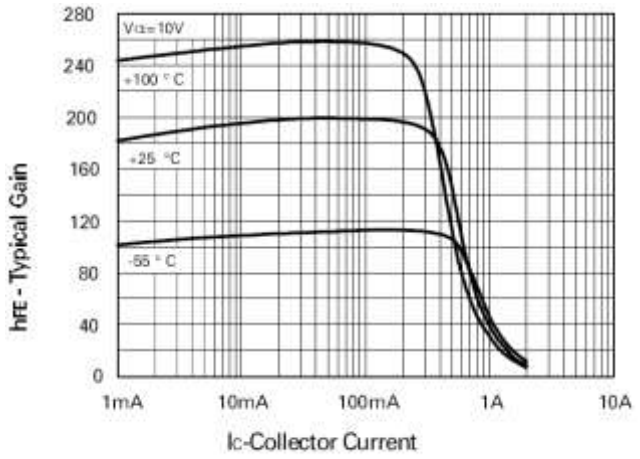
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



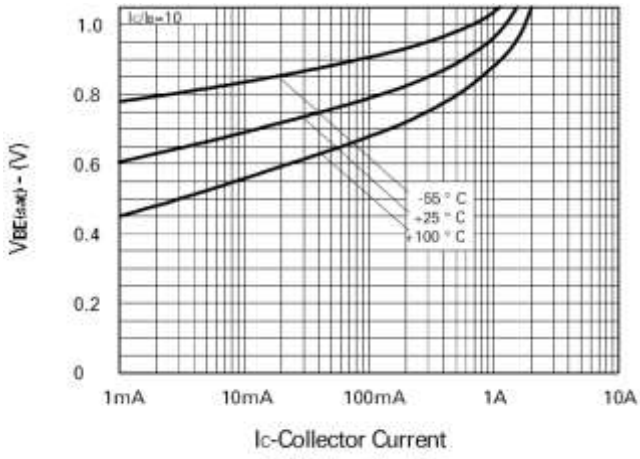
VCE(sat) v IC



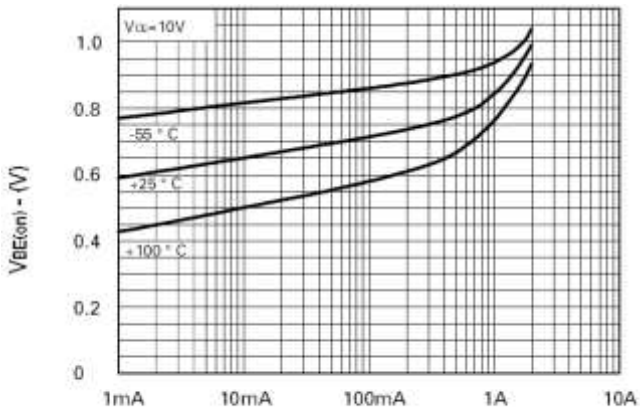
VCE(sat) v IC



hFE V IC



VBE(sat) v IC



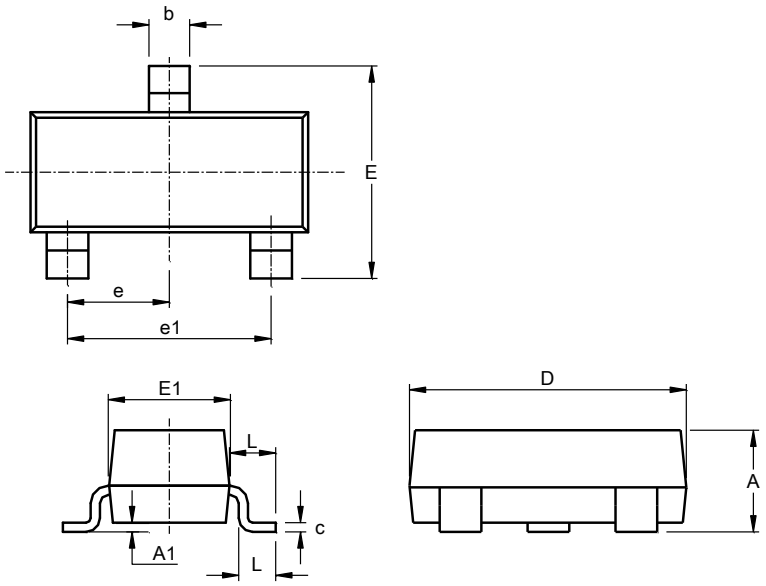
VBE(on) v IC

© Diodes Incorporated

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 Type DN

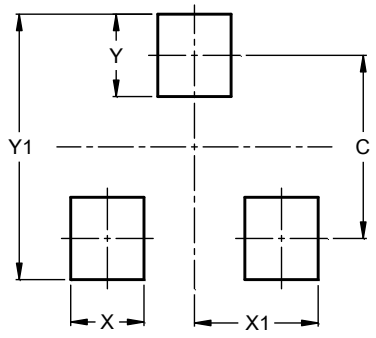


SOT23 Type DN			
Dim	**Min**	**Max**	**Typ**
A	0.89	1.12	1.00
A1	0.01	0.10	0.05
b	0.30	0.51	0.45
c	0.08	0.20	0.10
D	2.80	3.04	3.00
E	2.10	2.64	2.42
E1	1.20	1.40	1.37
e	0.95 REF		
e1	1.90 REF		
L	0.25	0.60	0.30
L1	0.45	0.62	0.54
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 Type DN



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

© Diodes Incorporated

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9